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36	14		EPO; JPO;	2004/09/29 15:52
		diamond (aluminum adj nitride) (boron adj nitride) (gallium adj	DERWENT;	
		nitride) (silicon adj nitride)) and (bandgap (band adj gap)) and	IBM_TDB	
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		diamond (aluminum adj nitride) (boron adj nitride) (gallium adj	DERWENT;	
		nitride) (silicon adj nitride)) and (diode transistor fet bjt bipolar	IBM_TDB	
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